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List of Publications by Year
in descending order

Version: 2024-02-01

29 papers	893 citations	516710 16 h-index	454955 30 g-index
32 all docs	32 docs citations	32 times ranked	1007 citing authors

#	Article	IF	Citations
1	Transparent flexible thermoelectric material based on non-toxic earth-abundant p-type copper iodide thin film. Nature Communications, 2017, 8, 16076.	12.8	233
2	Tin-assisted heteroepitaxial PLD-growth of Îº-Ga2O3 thin films with high crystalline quality. APL Materials, 2019, 7, .	5.1	98
3	Room-temperature Domain-epitaxy of Copper Iodide Thin Films for Transparent CuI/ZnO Heterojunctions with High Rectification Ratios Larger than 109. Scientific Reports, 2016, 6, 21937.	3.3	91
4	Heteroepitaxial growth of Î±-, Î²-, Î³- and Îº-Ga2O3 phases by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2019, 510, 76-84.	1.5	59
5	Epitaxial stabilization of single phase Îº-(InxGa1â^'x)2O3 thin films up to x = 0.28 on c-sapphire and Îº-Ga2O3(001) templates by tin-assisted VCCS-PLD. APL Materials, 2019, 7, .	5.1	38
6	Structural, optical, and electrical properties of orthorhombic Îº-(InxGa1â^'x)2O3 thin films. APL Materials, 2019, 7, .	5.1	34
7	Epitaxial Îº-(AlxGa1â^'x)2O3 thin films and heterostructures grown by tin-assisted VCCS-PLD. APL Materials, 2019, 7, .	5.1	30
8	Suppression of Grain Boundary Scattering in Multifunctional pâ€Type Transparent Î³â€CuI Thin Films due to Interface Tunneling Currents. Advanced Materials Interfaces, 2018, 5, 1701411.	3.7	26
9	Solubility limit and material properties of a Îº-(AlxGa1â^'x)2O3 thin film with a lateral cation gradient on (00.1)Al2O3 by tin-assisted PLD. APL Materials, 2020, 8, 021103.	5.1	26
10	A Review of the Segmentedâ€Target Approach to Combinatorial Material Synthesis by Pulsedâ€Laser Deposition. Physica Status Solidi (B): Basic Research, 2020, 257, 1900626.	1.5	26
11	Realization of highly rectifying Schottky barrier diodes and pn heterojunctions on Îº-Ga2O3 by overcoming the conductivity anisotropy. Journal of Applied Physics, 2021, 130, .	2.5	24
12	Growth, structural and optical properties of coherent Îº-(AlxGa1â^'x)2O3/Îº-Ga2O3 quantum well superlattice heterostructures. APL Materials, 2020, 8, .	5.1	24
13	Control of phase formation of (Al x Ga1â€‰â^'â€‰x)2O3 thin films on c-plane Al2O3. Journal Physics D: Applied Physics, 2020, 53, 485105.	2.8	24
14	Combinatorial Material Science and Strain Engineering Enabled by Pulsed Laser Deposition Using Radially Segmented Targets. ACS Combinatorial Science, 2018, 20, 643-652.	3.8	21
15	Modeling the electrical transport in epitaxial undoped and Ni-, Cr-, and W-doped TiO2 anatase thin films. Applied Physics Letters, 2014, 105, 062103.	3.3	20
16	Structural and Elastic Properties of Î±â€(Al_xGa_{1â^'x})₂O₃ Thin Films on (11.0) Al₂O₃ Substrates for the Entire Composition Range. Physica Status Solidi (B): Basic Research, 2021, 258, 2000394.	1.5	18
17	Valence band offsets for ALD SiO2 and Al2O3 on (InxGa1â^'x)2O3 for x = 0.25â€“0.74. APL Materials, 2019, 7, .	5.1	14
18	Band Offsets at Îº-([Al,In]_xGa_{1â€“x})₂O₃/MgO Interfaces. ACS Applied Materials & Interfaces, 2020, 12, 8879-8885.	8.0	14

#	Article	IF	Citations
19	Band Alignment of Atomic Layer Deposited SiO2 and Al2O3 on (AlxGa1-x)2O3 for x = 0.2-0.65. ECS Journal of Solid State Science and Technology, 2019, 8, P351-P356.	1.8	12
20	Strain states and relaxation for $$alpha$$-(Al$$_x$$Ga$$_{1-x}$$)$$_2$$O$$_3$$ thin films on prismatic planes of $$alpha$$-Al$$_2$$O$$_3$$ in the full composition range: Fundamental difference of a- and m-epitaxial planes in the manifestation of shear strain and lattice tilt. Journal of Materials Research, 2021, 36, 4816-4831.	2.6	9
21	Highly transparent conductors for optical and microwave access to spin-based quantum systems. Npj Quantum Information, 2019, 5, .	6.7	8
22	From high-T_csuperconductors to highly correlated Mott insulatorsâ€”25 years of pulsed laser deposition of functional oxides in Leipzig. Semiconductor Science and Technology, 2015, 30, 024003.	2.0	7
23	Epitaxial Growth of Î²â€(Al_xGa_{1â^'x})₂O₃ Layers and Superlattice Heterostructures up to xâ€‰=â€‰0.48 on Highly Conductive Alâ€Doped ZnO Thinâ€Film Templates by Pulsed Laser Deposition. Physica Status Solidi (B): Basic Research, 2021, 258, 2000359.	1.5	7
24	Band Offsets of Insulating & Semiconducting Oxides on (Al_xGa_{1-x})O₃. ECS Transactions, 2019, 92, 79-88.	0.5	6
25	Effect of Annealing on the Band Alignment of ALD SiO₂ on (Al_xGa_{1-x})₂O₃ for x = 0.2 - 0.65. ECS Journal of Solid State Science and Technology, 2019, 8, P751-P756.	1.8	6
26	Changes in band alignment during annealing at 600â€‰Â°C of ALD Al2O3 on (InxGa1â€‰â^'â€‰x)2O3 for xâ€‰=â€‰0.25â€“0.74. Journal of Applied Physics, 2020, 127, 105701.	2.5	6
27	Epitaxial growth of rhombohedral Î²-and cubic Î³-CuI. Journal of Crystal Growth, 2021, 570, 126218.	1.5	6
28	Method of full polarization control of microwave fields in a scalable transparent structure for spin manipulation. Journal of Applied Physics, 2020, 128, .	2.5	4
29	Annealing Effects on the Band Alignment of ALD SiO₂ on (In_xGa_{1â^'x})₂O₃ for x = 0.25â€“0.74. ECS Journal of Solid State Science and Technology, 2020, 9, 045001.	1.8	0